

Analysis of deep level spectrum in GaAs p+-p-i-n-n+ structures

Toompuu, Jana; Sleptšuk, Natalja; Korolkov, Oleg; Rang, Toomas Materials characterization VII 2015 / p. 283-294 : ill

Comparative characteristics of diffusion-welded high-voltage stacks and connected in series Schottky diodes

Sleptšuk, Natalja; Korolkov, Oleg; Land, Raul; Toompuu, Jana; Annus, Paul; Rang, Toomas BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 39-42 : ill http://www.ester.ee/record=b2150914*est

Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application

Sleptšuk, Natalja; Lebedev, Alexander A.; Eliseyev, Ilya; Korolkov, Oleg; Toompuu, Jana; Land, Raul; Mikli, Valdek; Zubov, Alexander; Rang, Toomas Modern Materials and Manufacturing 2019 : 12th International DAAAM Baltic Conference and 27th International Baltic Conference BALTMATRIB 2019. Selected, peer reviewed papers from the conference Modern Materials and Manufacturing 2019 (MMM 2019), April 24-26, 2019, Tallinn, Estonia 2019 / p. 185-190 : ill https://www.ester.ee/record=b5235278*est <https://www.scientific.net/KEM.799.185> <https://doi.org/10.4028/www.scientific.net/KEM.799.185> Conference proceeding at Scopus Article at Scopus

Comparison of individual SiC JBS chips and JBS stacks connected in series by diffusion welding

Sleptšuk, Natalja; Korolkov, Oleg; Toompuu, Jana; Rang, Toomas BEC 2010 : 2010 12th Biennial Baltic Electronics Conference : proceedings of the 12th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 4-6, 2010, Tallinn, Estonia 2010 / p. 81-84 : ill

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

Lebedev, Alexander A.; Davidovskaja, Klavdia; Kozlovski, Vitali V.; Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 447-450 : ill <https://doi.org/10.4028/www.scientific.net/MSF.897.447> Conference proceedings at Scopus Article at Scopus

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons

Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Diffusion welded contacts and related art applied to semiconductor materials

Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas Elektronika ir elektrotechnika = Electronics and electrical engineering 2011 / p. 67-70 : ill <https://eejournal.ktu.lt/index.php/elt/article/view/359>

DLTS measurements on 4H-SiC JBS-diodes with boron implanted local p-n junctions

Ivanov, Pavel; Korolkov, Oleg; Samsonova, Tatyana; Sleptšuk, Natalja; Potapov, Alexander; Toompuu, Jana; Rang, Toomas Materials science forum 2011 / p. 409-412 https://www.researchgate.net/publication/272046403_DLTS_measurements_on_4H-SiC_JBS-diodes_with_boron_implanted_local_p-n_junctions

A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation

Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; Korolkov, Oleg; Sleptšuk, Natalja Semiconductors 2011 / p. 1306-1310 : ill <https://doi.org/10.1134/S1063782611100101>

Electron microscopy study of contact layers in n-type 4H-SiC after diffusion welding

Korolkov, Oleg; Sleptšuk, Natalja; Sitnikova, A.; Rang, Toomas BEC 2008 : 2008 International Biennial Baltic Electronics Conference : proceedings of the 11th Biennial Baltic Electronics Conference : Tallinn University of Technology : October 6-8, 2008, Tallinn, Estonia 2008 / p. 91-94 : ill

Experimental study of surface distortions in silicon carbide caused by diffusion welding

Mizsei, Janos; Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas BEC 2012 : 2012 13th Biennial Baltic Electronics Conference : proceedings of the 13th Biennial Baltic Electronics Conference : October 3-5, 2012, Tallinn, Estonia 2012 / p. 53-56 : ill

GaAs based diffusion welded high voltage diode stacks [Electronic resource]

Toompuu, Jana; Korolkov, Oleg; Sleptšuk, Natalja; Voitoviš, Viktor; Rang, Toomas IEEE International Conference on Semiconductor Electronics CD-ROM Proceedings 2010 / [4] p <https://ieeexplore.ieee.org/document/5549505>

High voltage diffusion/welded stacks on the basis of SiC Schottky diodes

Korolkov, Oleg; Sleptšuk, Natalja; Annus, Paul; Land, Raul; Rang, Toomas ICSRM 2015 : program guide 2015 / p. 73

High-voltage diffusion/welded stacks on the basis of SiC Schottky diodes

Korolkov, Oleg; Sleptšuk, Natalja; Annus, Paul; Land, Raul; Rang, Toomas Silicon carbide and related materials 2015 (ICSRM 2015) : selected, peer reviewed papers from the 16th International Conference on Silicon Carbide and Related Materials, October 4-9, 2015, Giardini Naxos, Italy 2016 / p. 790-794 : ill <https://doi.org/10.4028/www.scientific.net/MSF.858.790> Conference Proceedings at

Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes

Kozlovski, Vitali V.; **Korolkov, Oleg**; Davydovskaya, Klavdia S.; Lebedev, Alexander A.; Levinshtein, Michael E.; **Sleptšuk, Natalja**; Strel'Chuk, Anatolii M.; **Toompuu, Jana** Technical Physics Letter 2020 / p. 287 - 289 <https://doi.org/10.1134/S1063785020030244>
[Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Intermediate layer in the metal-silicon carbide contact : investigation of the intermediate layer in the metal-silicon carbide contact obtained by diffusion weldin

Sleptšuk, Natalja 2012 <https://www.amazon.com/Intermediate-Layer-Metal-Silicon-Carbide-Contact/dp/3848422239>

Investigation of additional states in the silicon carbide surface after diffusion welding

Mizsei, Janos; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** ICSCRM2011 : Cleveland Ohio, USA, September 11-16, 2011 : abstracts 2011 / p. 356 : ill
https://www.researchgate.net/publication/269377410_Investigation_of_Additional_States_in_the_Silicon_Carbide_Surface_after_Diffusion_Welding

Investigation of deep level centers in i- and n-layers of GaAs pin-diodes

Toompuu, Jana; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Rang, Toomas** BEC 2014 : 2014 14th Biennial Baltic Electronics Conference : proceedings of the 14th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 6-8, 2014, Tallinn, Estonia 2014 / p. 25-28 : ill

Investigation of p-i-n GaAs structures by DLTS method

Toompuu, Jana; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Rang, Toomas** Elektronika ir elektrotehnika = Electronics and electrical engineering 2010 / 4, p. 51-54 : ill https://www.researchgate.net/publication/267372152_Investigation_of_p-i-n_GaAs_structures_by_DLTS_method

Investigation of the graphene-on-silicon-carbide and CVD graphene as a basis for bioimpedance sensor applications : poster

Sleptšuk, Natalja; **Land, Raul**; **Toompuu, Jana**; **Lebedev, Alexander A.**; Davydov, Valery; Eliseyev, Ilya; Kalinina, Evgenia; **Korolkov, Oleg**; **Rang, Toomas** ePosters 2018 / 1 p.: ill <https://cdn.technologynetworks.com/ep/pdfs/natalja-sleptsuk-a-raul-land-a-jana-toompuu-a-alexander-lebedev-b-valery-davydov-b-ilya-eliseyev-b.pdf>

Investigation of the intermediate layer in the metal-silicon carbide contact obtained by diffusion welding = Difusioonkeevitusega valmistatud metalli ja ränikarbiidi vahelise üleminekuala vahekihi uurimine

Sleptšuk, Natalja 2011 https://www.ester.ee/record=b2692547*est

Leakage currents in 4H-SiC JBS diodes

Ivanov, Pavel; **Korolkov, Oleg**; **Sleptšuk, Natalja** Semiconductors 2012 / p. 397-400 : ill
<https://link.springer.com/article/10.1134/S106378261203013X>

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Semiconductors 2019 / p. 975-978 <https://doi.org/10.1134/S1063782619070133> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p⁺-pin-n⁺ structures and result of analysis

Toompuu, Jana; **Sleptšuk, Natalja**; **Korolkov, Oleg**; **Rang, Toomas** BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 35-38 : ill http://www.ester.ee/record=b2150914*est

New interdisciplinary master program in communicative electronics at Tallinn University of Technology

Rang, Toomas; **Sleptšuk, Natalja** 5th International Conference on Interdisciplinarity in Education ICIE'10 : New Higher Education Programs, June 17-19, 2010, Tallinn, Estonia : proceedings 2010 / p. 187-190 : ill

Pulsed laser deposition of Zn(O,Se) layers in nitrogen background pressure

Abdalla, Akram; **Bereznev, Sergei**; **Spalatu, Nicolae**; **Volobujeva, Olga**; **Sleptšuk, Natalja**; **Danilson, Mati** Scientific reports 2019 / art. 17443, 10 p. : ill <https://doi.org/10.1038/s41598-019-54008-1> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

SiC JBS diode symmetrical voltage doubler represented as the diffusion-welded stack

Korolkov, Oleg; **Land, Raul**; **Toompuu, Jana**; **Sleptšuk, Natalja**; **Rang, Toomas** Silicon carbide and related materials 2017 : ICSCRM 2017 : selected, peer reviewed papers from the 2017 International Conference on Silicon Carbide and related materials, September 17-22, 2017, Washington, DC, USA 2018 / p. 862-865 : ill <https://doi.org/10.4028/www.scientific.net/MSF.924.862> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

SiC schottky diode rectifier bridge represented as the diffusion-welded stack

Korolkov, Oleg; Land, Raul; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 42

SiC schottky diode rectifier bridge represented as the diffusion-welded stack

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; Land, Raul; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas

Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 697-700 : ill

<https://doi.org/10.4028/www.scientific.net/MSF.897.697> Conference proceedings at Scopus Article at Scopus

The dependence of reverse recovery time on barrier capacitance and series on-resistance in Schottky diodes

Veher, Oleksandr; Sleptšuk, Natalja; Toompuu, Jana; Korolkov, Oleg; Rang, Toomas Materials and contact characterisation

VIII 2017 / p. 15-22 : ill <https://doi.org/10.2495/MC170021> Conference proceedings at Scopus Article at Scopus

The measurement and tuning of SiC diode voltage doubler represented as diffusion-welded stack [Online resource]

Toompuu, Jana; Sleptšuk, Natalja; Land, Raul; Korolkov, Oleg; Rang, Toomas BEC 2018 : 2018 16th Biennial Baltic

Electronics Conference (BEC) : proceedings of the 16th Biennial Baltic Electronics Conference, October 8-10, 2018 2018 / 4 p.: ill

<https://doi.org/10.1109/BEC.2018.8600963>

The specificity of solid-phase interaction of aluminium with silicon carbide in the manufacture of diffusion-welded contacts to semiconductor devices

Sleptšuk, Natalja; Korolkov, Oleg; Toompuu, Jana; Rang, Toomas; Mikli, Valdek Elektronika ir elektrotechnika = Electronics

and electrical engineering 2012 / p. 45-48 : ill <https://eejournal.ktu.lt/index.php/elt/article/view/2610>

Исследование р-п-переходов на основе 4H-SiC, изготовленных имплантацией бора, методом нестационарной емкостной спектроскопии

Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; Korolkov, Oleg; Sleptšuk, Natalja Физика и техника полупроводников

2011 / с. 1358-1362 : ил

Низкотемпературный отжиг слаболегированных слоев n-4H-SiC после облучения быстрыми электронами

Korolkov, Oleg; Kozlovski, Vitali; Lebedev, Alexander; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas Физика и техника

полупроводников 2019 / с. 991-994 <https://doi.org/10.21883/FTP.2019.07.47879.9089>